# Applications of Accelerated Molecular Dynamics in Materials Science

### Blas Pedro Uberuaga

### Los Alamos National Laboratory



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### **Brief Introduction to Accelerated Molecular Dynamics**

- Many processes occur on much longer timescales than accessible via MD (ps-ns-μs)
  - e.g. surface growth
  - radiation damage annealing
  - mass transport
  - etc.
- Need method to reach experimentally relevant timescales
- Three accelerated dynamics methods developed at LANL (Art Voter's team)
  - Parallel-Replica Dynamics
  - Hyperdynamics
  - Temperature Accelerated Dynamics (TAD)





Parallel Replica Dynamics (1998)	Explore basin with many processors $M$ such that $M \sim \tau_{rxn}/1$ ps



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Parallel Replica Dynamics (1998)	Explore basin with many processors <i>M</i> such that <i>M</i> ~τ <sub>rxn</sub> /1 ps
Hyperdynamics (1997)	Increase rate by reducing effective barriers
Temperature Accelerated Dynamics (2000)	Increase rate by raising temperature





### **Demonstrations of AMD methods**

- Vacancy Void Annealing in Cu
- Defect Dynamics in MgO
- Strain-rate dependent behavior in wires and nanotubes





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### Common Theme: Examples where achieving long times in atomistic simulations provided critical insight





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A Parallel-Replica Study

## VACANCY VOID ANNEALING IN CU



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### Vacancy void annealing in Cu

- Goal:
  - Understand vacancy aggregation/void formation
  - Probe kinetics of vacancy voids
- Method:
  - Parallel-replica dynamics: explore long-time behavior of voids
  - Molecular dynamics: obtain statistics on possible pathways
  - Nudged elastic band (molecular statics): characterize pathways
- Reference:
  - Uberuaga, Voter, Hoagland, and Valone, PRL 99, 135501 (2007).





### Long time annealing of 20 vacancy void in Cu

- EAM Cu
- Parallel-replica simulation of 20vacancy void annealing at 400 K
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- Total simulation is 7.82 μs
- At 1.69 μs, void transforms to SFT
- Run on 39 processors for 15 days
- Efficiency = 79%
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New transformation pathway for the formation of stacking fault tetrahedra (SFTs)





### **Transformation pathway for 20 vacancy void**

- Full path for transformation to SFT calculated with NEB
- Initial barrier is > 2 eV
  - Should have taken
    >10<sup>5</sup> years at 400K
    to occur (assuming standard prefactor)
- Vineyard prefactor for first step between 10<sup>36</sup> and 10<sup>43</sup> Hz







### Void to SFT transformation: 45 vacancy void in Cu

- Par-rep of 45 vacancy void at 475 K
  - 39 processors
  - 39% efficiency
  - 5.6 days
    - Effective 1 CPU time: 85 days
  - 0.24 μs
- Figure is minimum energy path at constant volume
- Overcomes a very large internal energy barrier (~4 eV) at 475 K
- Free energy barrier is much lower, as estimated by open symbols









### Initial step in void to SFT transformation

- Barrier to initiate transformation accessible from a number of states
- Part of path is a ridge, minimizing along it can land to either lower energy state
  - Problem for ensuring connectivity of saddles
- Vineyard rate for 2.1 eV process very fast
  - 144 ns at 400 K
  - About 1 fs at 500 K
  - Harmonic TST valid?
  - TAD valid?





### **Prefactor for Transformation**

- Barrier for 20-vacancy void is between 2.3 and 2.7 eV
  - Assuming a standard prefactor (~10<sup>13</sup> Hz), would take 10<sup>6</sup> years to occur at T=400 K
  - Observed waiting times are 1-15 ns
  - Prefactor observed from dynamics: 10<sup>38</sup> Hz; calculated with Vineyard: 10<sup>43</sup> Hz
  - Prefactor is anything but standard!
- Origin of Prefactor
  - View material containing void as partitioned into two regions
    - Region I: Cu
    - Region II: void
  - Before transition, volume of Cu is Region I volume
  - After, volume of Cu is Region I + Region II
  - Entropy change  $\Delta S$  due to volume change  $\Delta V: \Delta S = \alpha B \Delta V$ 
    - $\alpha$ =coefficient of thermal expansion, B=bulk modulus
  - Assuming ∆V=10 atomic volumes ⇒ ∆S=67.5/k<sub>B</sub> ⇒ prefactor enhanced by factor of 10<sup>29</sup>
  - Consistent with observed/calculated prefactor







### Why long time simulations were needed?

- Once system is in corner state, time scale for void → SFT transformation very quick, ns
- However, time to reach corner state can be very long, 1.7 μs at 400 K
- Parallel-replica was critical for reaching time scales for surface vacancy to sample surface configurations and discover corner state
- HTST-based methods may have failed to predict mechanism





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A Temperature Accelerated Dynamics Study

### **DEFECT DYNAMICS IN MGO**



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### **Defect Dynamics in MgO**

- Goal:
  - Understand origin of radiation tolerance in complex oxides
  - Determine the relevance of metastable defects
- Methods:
  - Buckingham potential with long range electrostatics
  - MD: non-equilibrium production of damage due to irradiation
  - TAD: evolution of defects produced under irradiation
  - Rate theory: impact of atomistic defect properties on experimental observables
- References:
  - Uberuaga, Smith, Cleave, Henkelman, Grimes, Voter, and Sickafus,
    PRL 92, 115505 (2004); PRB 71, 104102 (2005); NIMB 28, 260 (2005).





### TAD Simulation: Long-range Annihilation

- Begin with I<sub>2</sub> and two vacancies
- I<sub>2</sub> attracted to charged vacancies, annihilating by 81 ms
- Annihilation via long range, concerted events involving many atoms
- Red=oxygen, Blue=magnesium
- Dark=interstitial, Light=vacancy







### **Defect aggregation in MgO**

- Begin with I<sub>2</sub> and I<sub>4</sub>
  - Defects found at end of collision cascade
- $I_2$  attracted to  $I_4$ , binds forming  $I_6$
- Metastable I<sub>6</sub> diffuses very quickly
  - ns timescale at 300 K
  - diffusion is 1D along <110>
  - decay to ground state takes years
- Red=oxygen, Blue=magnesium
- Dark=interstitial, Light=vacancy



TAD simulation, Uberuaga et al, 2003



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### Cluster dynamics: Kinetics of the pentamer cluster in MgO

- Two versions of pentamer:
  - $-Mg_2O_3$
  - $-Mg_3O_2$
- Both can exist in 3 forms
- Each has unique diffusive characteristics
  - A: diffuses quickly in <110> direction
  - B: diffuses more slowly, again in <110> direction
  - C: immobile at 300K
- A, B and C behave similarly for both pentamers
- But decay between forms is different



Encounters of MgO+MgO<sub>2</sub> can form any type of Mg<sub>2</sub>O<sub>3</sub> – 10 simulations: 1 forms A, 7 form B, 2 form C

> Uberuaga, et. al., *PRL* **92**, 115505 (2004); *PRB* **72**, (2005); *NIMB* **28**, 260 (2005)



### Interstitial cluster kinetics in MgO

- Diffusion barrier of ground state structures follow no clear pattern
- For clusters of size 5 and greater, there are metastable structures that diffuse faster than the ground state





Uberuaga, et. al., *PRL* **92**, 115505 (2004); *PRB* **72**, (2005); *NIMB* **28**, 260 (2005)



### **Effects of cluster mobility on observables**

- 1-D reaction rate theory
  - Mobilities from TAD
  - Steady-state conditions
- Size of loops increases by more than 3 times when large clusters are mobile
  - "large" clusters contain more than 1 interstitial
- Enhanced defect mobility results in fewer, larger loops





Uberuaga, et. al., *PRL* **92**, 115505 (2004); *PRB* **72**, (2005); *NIMB* **28**, 260 (2005)



### Why long time simulations were needed?

- TAD simulations revealed that aggregation of interstitials leads to metastable interstitial cluster structures with high mobilities
- Critical that evolution observed at low temperature as lifetime of metastable clusters at high temperature would be short and possibly missed if simply performed hightemperature MD
  - Decay barriers 0.5 2 eV
  - Migration barriers 0.3 2 eV





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Two Parallel-Replica Studies

## STRAIN-RATE DEPENDENT BEHAVIOR



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### ParRep of stretching Ag nanowire

- Run on LANL Roadrunner (1 PFLOPS if using all 12,240 cell processors)
- Boost good at first; drops as events become more frequent.
- Outer edge atoms clamped, advanced 0.01A at regular intervals

Ag[110] nanowire, 1.d5 A/s, 1 us per frame



### **Pulling slower changes behavior**

At stretching speeds below ~10<sup>6</sup> Å/s, the system can thin down, coming back to perfect fcc. At higher speeds, it disorders or necks, never recovering perfect fcc.



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### **Structure of Nanotubes after Yield**



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### **Energy vs Strain for Nanotube with a Vacancy**



### Why long time simulations were needed?

- In both nanowire and nanotube, new processes occur as strain rate is decreased
- These processes relieve strain in a qualitatively differently manner than in over-driven cases
- Observation of these processes depends on reducing strain rates by reaching longer time scales





### Summary

- AMD methods allow the study of processes not accessible to MD
- Often, results are very surprising
  - Many mechanisms that would be left out of e.g. KMC if intuition alone is used
  - New insights into kinetic processes, even in the simplest of materials

# Probing long-time kinetics is crucial for understanding material evolution in complex environments



